Attorney Docket No. 040021-0306970 Client Reference: OPP 030892 US

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

KWAN-JU KOH

Application No.:

Confirmation

No:

Filed:

December 3, 2003

Group No.:

Examiner

For:

MOS TRANSISTOR AND FABRICATION METHOD THEREOF

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

APPLICATION DATA SHEET 37 C.F.R. § 1.76

BIBLIOGRAPHIC DATA

1. Applicant information

First applicant: KWAN-JU KOH

Citizenship: KOREA Residence: Seoul, Korea

2. Correspondence information

Correspondence for this application should be addressed as follows:

Customer No.: 00909

3. Application information

Title of Invention: MOS TRANSISTOR AND FABRICATION METHOD THEREOF

Docket number assigned to this application: 040021-0306970

Suggested Classification:

Class:

Subclass:

Technology Center to which subject matter is assigned:

Total number of drawing sheets: 2

Type of application:

Utility

Application is to be published. Suggested drawing figure for publication: 2E

Secrecy order under § 5.2:

This application does not disclose subject matter of an application which is under a secrecy order pursuant to § 5.2.

4. Representative information

The following have a power of attorney or authorization of agent in this application:

Customer No.: 00909

5. Foreign priority information

Foreign priority is claimed for this application as follows:

Country: KOREA

Application No.: 10-2002-0076823 Filing Date: December 5, 2002

Status: pending

6. Assignee information

The assignee(s) of this application is/are:

Anam Semiconductor Inc. 891-10, Daechi-dong, Kangnam-ku Seoul, 135-523 KOREA

Extent of interest of assignee in application: 100%

Date: December 3, 2003

Reg. No.: 38705

Tel. No.: (703) 905-2011 Customer No.: 00909 Signature of Practitioner

Glenn T. Barrett

PILLSBURY WINTHROP LLP

P.O. Box 10500 McLean, VA 22102